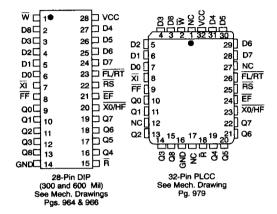
DALLASSEMICONDUCTOR

DS2010 1024 x 9 FIFO Chip

FEATURES

- · First-in, first-out memory-based architecture
- Flexible 1024 x 9 organization
- Low-power HCMOS technology
- Asychronous and simultaneous read/write
- Bidirectional applications
- · Fully expandable by word width or depth
- Empty and full warning flags
- Half-full flag capability in single-device mode
- Retransmit capability
- Available in 50ns, 65ns, 80ns, and 120ns access times
- Optional industrial temperature range -40°C to +85°C available, designated N

PIN ASSIGNMENT



PIN DESCRIPTION

W WRITE R READ RS RESET **FL/RT** First Load/Retransmit Data In D₀₋₈ Q_{0-8} Data Out ΧĪ - Expansion In XO/HF Expansion Out/Half Full FF Full Flag EF **Empty Flag** 5 Volts Vcc - Ground **GND** No Connect NC

DESCRIPTION

The DS2010 FIFO Chip implements a first-in, first-out algorithm featuring asynchronous read/write operations, full, empty, and half-full flags, and unlimited expansion capability in both word size and depth. The DS2010 is functionally and electrically equivalent to the

DS2009 512 x 9 FIFO, with the exceptions listed in the notes for DC Electrical Characteristics of the DS2009 data sheet. Refer to the DS2009 data sheet for detailed device description.

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